

L Number	Hits	Search Text	DB	Time stamp
1	1	"20030008505"	US-PGPUB	2003/08/20 17:26
2	2	(silicide same (self near2 grow\$3)) same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:57
3	1093	(silicide same grow\$3) same (silicon same etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:32
4	0	((silicide same grow\$3) same (silicon same etch\$3)) same (nano near wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:32
5	0	(silicide same grow\$3) same (nano near wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:32
6	14	grow\$3 same (nano near wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:32
7	5920	silicide same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 17:57
8	96	(silicide same silicon) same ((anisotropic\$4 near etch\$3) same silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 20:00
10	0	((silicide same silicon) same ((anisotropic\$4 near etch\$3) same silicon)) and @pd<20011113 and (nano near wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 18:00
9	77	((silicide same silicon) same ((anisotropic\$4 near etch\$3) same silicon)) and @pd<20011113	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 18:00
11	17532	(anisotropic\$4 near etch\$3) same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 18:03
12	59	((anisotropic\$4 near etch\$3) same silicon) same (mask\$3 near5 silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 18:03
13	42	((anisotropic\$4 near etch\$3) same silicon) same (mask\$3 near5 silicide)) and @pd<20011113	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 18:43
14	14	(nano near wire) same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:38

15	0	(nano near wire or nano near structure or nano near pattern) same ((epitaxial\$2 near grow\$3) same silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:41
16	1	(nano near wire or nano near structure or nano near pattern) same (epitaxial\$2 near grow\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:45
17	154062	(etch\$3 or pattern\$3) same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:45
18	1548	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:46
19	0	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) same nano	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:47
20	1213	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano structure))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:54
21	936	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano structure))) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:48
22	0	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano structure))) and insulat\$3) and @pd<2001626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:50
23	532	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano structure))) and insulat\$3) and @pd<20010626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:54
24	1	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano structure))) and insulat\$3) and @pd<20010626) and 216/41.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:52
25	0	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano near structure))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:56
26	0	((etch\$3 or pattern\$3) same silicon) same (mask\$3 with silicide)) and ((nano near wire) or (nano near structure))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 19:56
27	45	((silicide same silicon) same ((anisotropic\$4 near etch\$3) same silicon)) and (insulat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 20:00